

ABSTRACT

A method of forming an SOI substrate including a hydrogen thermal treatment performed on a pretreated sacrificial wafer, under high temperature. A stopper layer and a semiconductor layer may be sequentially formed on a first surface of the sacrificial wafer on which the hydrogen (H₂) thermal treatment was performed. The stopper layer and the semiconductor layer may be formed by an epitaxial growth process using a mixed precursor including a monosilane (MS) source and a dichlorosilane (DCS) source.

FIG. 2